

# ON Semiconductor

## Is Now

# onsemi™

To learn more about onsemi™, please visit our website at  
[www.onsemi.com](http://www.onsemi.com)

**onsemi** and **onsemi** and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "**onsemi**" or its affiliates and/or subsidiaries in the United States and/or other countries. **onsemi** owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of **onsemi** product/patent coverage may be accessed at [www.onsemi.com/site/pdf/Patent-Marking.pdf](http://www.onsemi.com/site/pdf/Patent-Marking.pdf). **onsemi** reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and **onsemi** makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using **onsemi** products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by **onsemi**. "Typical" parameters which may be provided in **onsemi** data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. **onsemi** does not convey any license under any of its intellectual property rights nor the rights of others. **onsemi** products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use **onsemi** products for any such unintended or unauthorized application, Buyer shall indemnify and hold **onsemi** and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that **onsemi** was negligent regarding the design or manufacture of the part. **onsemi** is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner. Other names and brands may be claimed as the property of others.

# MC74VHC374

## Octal D-Type Flip-Flop with 3-State Output

The MC74VHC374 is an advanced high speed CMOS octal flip–flip with 3–state output fabricated with silicon gate CMOS technology. It achieves high speed operation similar to equivalent Bipolar Schottky TTL while maintaining CMOS low power dissipation.

This 8–bit D–type flip–flip is controlled by a clock input and an output enable input. When the output enable input is high, the eight outputs are in a high impedance state.

The internal circuit is composed of three stages, including a buffer output which provides high noise immunity and stable output. The inputs tolerate voltages up to 7V, allowing the interface of 5V systems to 3V systems.

### Features

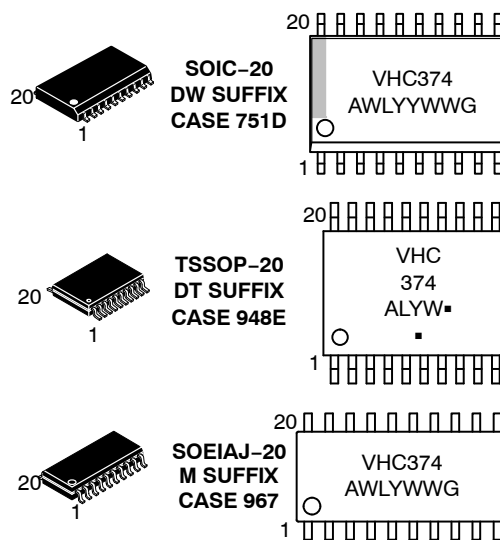
- High Speed:  $f_{max} = 185$  MHz (Typ) at  $V_{CC} = 5$  V
- Low Power Dissipation:  $I_{CC} = 4$   $\mu$ A (Max) at  $T_A = 25^\circ$ C
- High Noise Immunity:  $V_{NIH} = V_{NIL} = 28\%$   $V_{CC}$
- Power Down Protection Provided on Inputs
- Balanced Propagation Delays
- Designed for 2 V to 5.5 V Operating Range
- Low Noise:  $V_{OLP} = 0.9$  V (Max)
- Pin and Function Compatible with Other Standard Logic Families
- Latchup Performance Exceeds 300 mA
- ESD Performance: HBM > 2000 V; Machine Model > 200 V
- Chip Complexity: 266 FETs or 66.5 Equivalent Gates
- These Devices are Pb–Free and are RoHS Compliant



**ON Semiconductor®**

<http://onsemi.com>

### MARKING DIAGRAMS



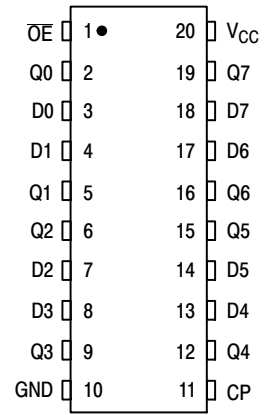
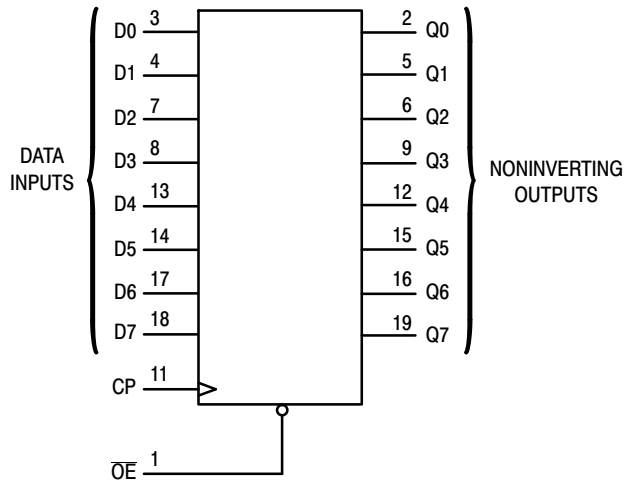
VHC374 = Specific Device Code  
 A = Assembly Location  
 WL, L = Wafer Lot  
 Y = Year  
 WW, W = Work Week  
 G or ■ = Pb–Free Package  
 (Note: Microdot may be in either location)

### ORDERING INFORMATION

Device	Package	Shipping†
MC74VHC374DWR2G	SOIC–20	1000 Units/Reel
MC74VHC374DTR2G	TSSOP–20	2500 Units/T&R
MC74VHC374MELG	SOEIAJ–20	2000 Units/Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

# MC74VHC374



## FUNCTION TABLE

INPUTS			OUTPUT
OE	CP	D	Q
L	↗	H	H
L	↘	L	L
L	L, H, ↗	X	No Change
H	X	X	Z

# MC74VHC374

## MAXIMUM RATINGS\*

Symbol	Parameter	Value	Unit
V <sub>CC</sub>	DC Supply Voltage	- 0.5 to + 7.0	V
V <sub>in</sub>	DC Input Voltage	- 0.5 to + 7.0	V
V <sub>out</sub>	DC Output Voltage	- 0.5 to V <sub>CC</sub> + 0.5	V
I <sub>IK</sub>	Input Diode Current	- 20	mA
I <sub>OK</sub>	Output Diode Current	± 20	mA
I <sub>out</sub>	DC Output Current, per Pin	± 25	mA
I <sub>CC</sub>	DC Supply Current, V <sub>CC</sub> and GND Pins	± 75	mA
P <sub>D</sub>	Power Dissipation in Still Air, SOIC Packages† TSSOP Package†	500 450	mW
T <sub>stg</sub>	Storage Temperature	- 65 to + 150	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation, V<sub>in</sub> and V<sub>out</sub> should be constrained to the range GND ≤ (V<sub>in</sub> or V<sub>out</sub>) ≤ V<sub>CC</sub>. Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V<sub>CC</sub>). Unused outputs must be left open.

\* Absolute maximum continuous ratings are those values beyond which damage to the device may occur. Exposure to these conditions or conditions beyond those indicated may adversely affect device reliability. Functional operation under absolute-maximum-rated conditions is not implied.

† Derating — SOIC Packages: - 7 mW/°C from 65° to 125°C  
TSSOP Package: - 6.1 mW/°C from 65° to 125°C

## RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V <sub>CC</sub>	DC Supply Voltage	2.0	5.5	V
V <sub>in</sub>	DC Input Voltage	0	5.5	V
V <sub>out</sub>	DC Output Voltage	0	V <sub>CC</sub>	V
T <sub>A</sub>	Operating Temperature	- 40	+ 85	°C
t <sub>r</sub> , t <sub>f</sub>	Input Rise and Fall Time	V <sub>CC</sub> = 3.3V V <sub>CC</sub> = 5.0V	0 100 20	ns/V

## DC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Test Conditions	V <sub>CC</sub> V	T <sub>A</sub> = 25°C			T <sub>A</sub> = - 40 to 85°C		Unit
				Min	Typ	Max	Min	Max	
V <sub>IH</sub>	Minimum High-Level Input Voltage		2.0 3.0 to 5.5	1.50 V <sub>CC</sub> × 0.7			1.50 V <sub>CC</sub> × 0.7		V
V <sub>IL</sub>	Maximum Low-Level Input Voltage		2.0 3.0 to 5.5			0.50 V <sub>CC</sub> × 0.3		0.50 V <sub>CC</sub> × 0.3	V
V <sub>OH</sub>	Minimum High-Level Output Voltage	V <sub>in</sub> = V <sub>IH</sub> or V <sub>IL</sub> I <sub>OH</sub> = - 50μA	2.0 3.0 4.5	1.9 2.9 4.4	2.0 3.0 4.5		1.9 2.9 4.4		V
		V <sub>in</sub> = V <sub>IH</sub> or V <sub>IL</sub> I <sub>OH</sub> = - 4mA I <sub>OH</sub> = - 8mA	3.0 4.5	2.58 3.94			2.48 3.80		
V <sub>OL</sub>	Maximum Low-Level Output Voltage	V <sub>in</sub> = V <sub>IH</sub> or V <sub>IL</sub> I <sub>OL</sub> = 50μA	2.0 3.0 4.5		0.0 0.0 0.0	0.1 0.1 0.1		0.1 0.1 0.1	V
		V <sub>in</sub> = V <sub>IH</sub> or V <sub>IL</sub> I <sub>OL</sub> = 4mA I <sub>OL</sub> = 8mA	3.0 4.5			0.36 0.36		0.44 0.44	

# MC74VHC374

## DC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Test Conditions	V <sub>CC</sub> V	T <sub>A</sub> = 25°C			T <sub>A</sub> = - 40 to 85°C		Unit
				Min	Typ	Max	Min	Max	
I <sub>in</sub>	Maximum Input Leakage Current	V <sub>in</sub> = 5.5V or GND	0 to 5.5			± 0.1		± 1.0	μA
I <sub>OZ</sub>	Maximum Three-State Leakage Current	V <sub>in</sub> = V <sub>IL</sub> or V <sub>IH</sub> V <sub>out</sub> = V <sub>CC</sub> or GND	5.5			± 0.25		± 2.5	μA
I <sub>CC</sub>	Maximum Quiescent Supply Current	V <sub>in</sub> = V <sub>CC</sub> or GND	5.5			4.0		40.0	μA

## AC ELECTRICAL CHARACTERISTICS (Input t<sub>r</sub> = t<sub>f</sub> = 3.0ns)

Symbol	Parameter	Test Conditions	T <sub>A</sub> = 25°C			T <sub>A</sub> = - 40 to 85°C		Unit
			Min	Typ	Max	Min	Max	
f <sub>max</sub>	Maximum Clock Frequency (50% Duty Cycle)	V <sub>CC</sub> = 3.3 ± 0.3V C <sub>L</sub> = 15pF	80	130		70		ns
		C <sub>L</sub> = 50pF	55	85		50		
t <sub>pLH</sub> , t <sub>pHL</sub>	Maximum Propagation Delay, CP to Q	V <sub>CC</sub> = 3.3 ± 0.3V C <sub>L</sub> = 15pF		8.1	12.7	1.0	15.0	ns
		C <sub>L</sub> = 50pF		10.6	16.2	1.0	18.5	
t <sub>pZL</sub> , t <sub>pZH</sub>	Output Enable Time, OE to Q	V <sub>CC</sub> = 3.3 ± 0.3V C <sub>L</sub> = 15pF		7.1	11.0	1.0	13.0	ns
		R <sub>L</sub> = 1kΩ C <sub>L</sub> = 50pF		9.6	14.5	1.0	16.5	
t <sub>pLZ</sub> , t <sub>pHZ</sub>	Output Disable Time, OE to Q	V <sub>CC</sub> = 5.0 ± 0.5V C <sub>L</sub> = 15pF		5.1	7.6	1.0	9.0	ns
		R <sub>L</sub> = 1kΩ C <sub>L</sub> = 50pF		6.6	9.6	1.0	11.0	
t <sub>OSLH</sub> , t <sub>OSHL</sub>	Output to Output Skew	V <sub>CC</sub> = 3.3 ± 0.3V C <sub>L</sub> = 50pF			1.5		1.5	ns
		(Note 1)						
C <sub>in</sub>	Maximum Input Capacitance	V <sub>CC</sub> = 5.0 ± 0.5V C <sub>L</sub> = 50pF						pF
		R <sub>L</sub> = 1kΩ						
C <sub>out</sub>	Maximum Three-State Output Capacitance (Output in High-Impedance State)	V <sub>CC</sub> = 3.3 ± 0.3V C <sub>L</sub> = 50pF			1.5		1.5	ns
		(Note 1)						
C <sub>in</sub>	Maximum Input Capacitance			4	10		10	pF
C <sub>out</sub>	Maximum Three-State Output Capacitance (Output in High-Impedance State)			6				pF

C <sub>PD</sub>	Power Dissipation Capacitance (Note 2)	Typical @ 25°C, V <sub>CC</sub> = 5.0V	
		Value	Unit
		32	pF

- Parameter guaranteed by design. t<sub>OSLH</sub> = |t<sub>pLHm</sub> - t<sub>pLHn</sub>|, t<sub>OSHL</sub> = |t<sub>pHLm</sub> - t<sub>pHLn</sub>|.
- C<sub>PD</sub> is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: I<sub>CC(OPR)</sub> = C<sub>PD</sub> • V<sub>CC</sub> • f<sub>in</sub> + I<sub>CC</sub>/8 (per flip-flop). C<sub>PD</sub> is used to determine the no-load dynamic power consumption; P<sub>D</sub> = C<sub>PD</sub> • V<sub>CC</sub><sup>2</sup> • f<sub>in</sub> + I<sub>CC</sub> • V<sub>CC</sub>.

# MC74VHC374

## NOISE CHARACTERISTICS (Input $t_r = t_f = 3.0\text{ns}$ , $C_L = 50\text{pF}$ , $V_{CC} = 5.0\text{V}$ )

Symbol	Parameter	$T_A = 25^\circ\text{C}$		Unit
		Typ	Max	
$V_{OLP}$	Quiet Output Maximum Dynamic $V_{OL}$	0.6	0.9	V
$V_{OLV}$	Quiet Output Minimum Dynamic $V_{OL}$	-0.6	-0.9	V
$V_{IHD}$	Minimum High Level Dynamic Input Voltage		3.5	V
$V_{ILD}$	Maximum Low Level Dynamic Input Voltage		1.5	V

## TIMING REQUIREMENTS (Input $t_r = t_f = 3.0\text{ns}$ )

Symbol	Parameter	Test Conditions	$T_A = 25^\circ\text{C}$		$T_A = -40$ to $85^\circ\text{C}$	Unit
			Typ	Limit	Limit	
$t_w$	Minimum Pulse Width, CP	$V_{CC} = 3.3 \pm 0.3\text{ V}$ $V_{CC} = 5.0 \pm 0.5\text{ V}$		5.0 5.0	5.5 5.0	ns
$t_{su}$	Minimum Setup Time, D to CP	$V_{CC} = 3.3 \pm 0.3\text{ V}$ $V_{CC} = 5.0 \pm 0.5\text{ V}$		4.5 3.0	4.5 3.0	ns
$t_h$	Minimum Hold Time, D to CP	$V_{CC} = 3.3 \pm 0.3\text{ V}$ $V_{CC} = 5.0 \pm 0.5\text{ V}$		2.0 2.0	2.0 2.0	ns
$t_r, t_f$	Maximum Input Rise and Fall Times	$V_{CC} = 3.3 \pm 0.3\text{ V}$ $V_{CC} = 5.0 \pm 0.5\text{ V}$				ns

## SWITCHING WAVEFORMS

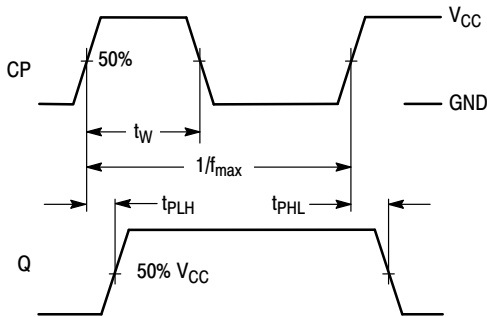


Figure 3.

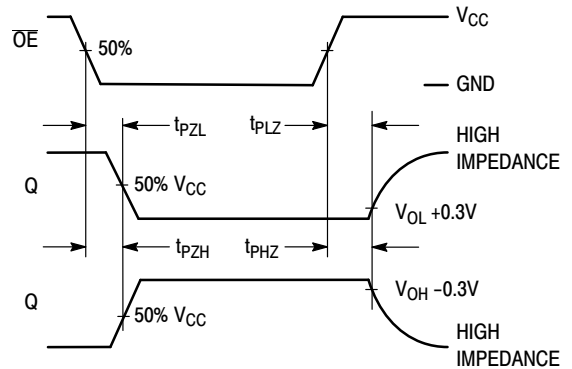


Figure 4.

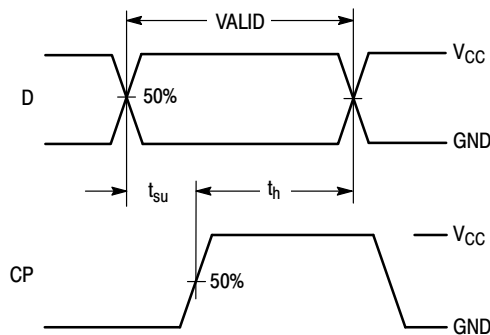
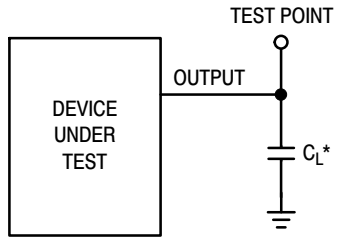


Figure 5.

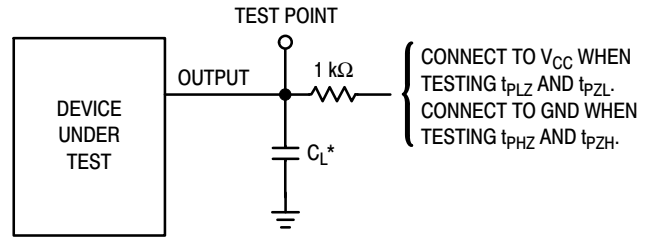
# MC74VHC374

## TEST CIRCUITS



\*Includes all probe and jig capacitance

Figure 6.



\*Includes all probe and jig capacitance

Figure 7.

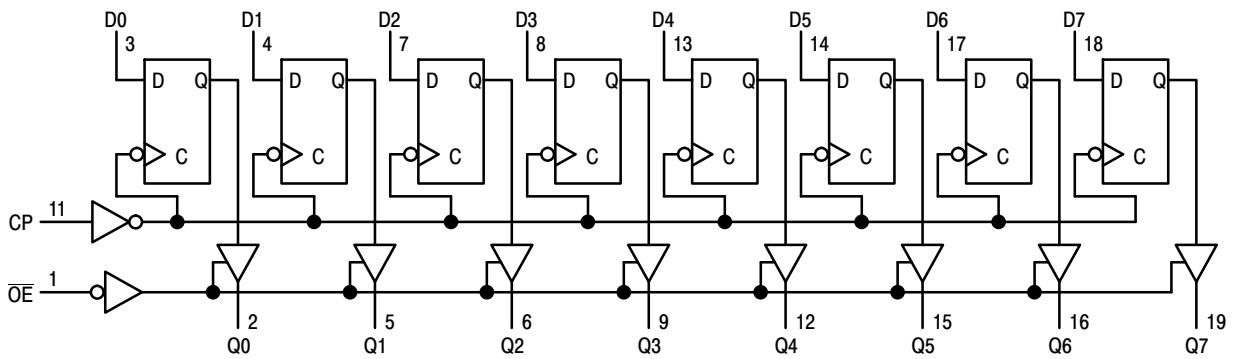


Figure 8. EXPANDED LOGIC DIAGRAM

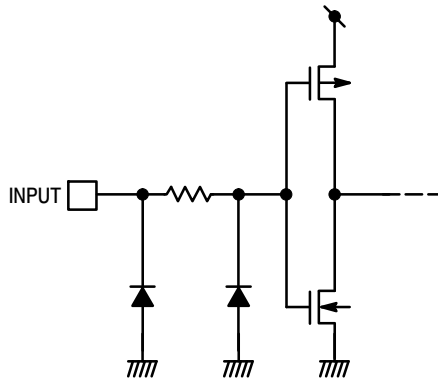
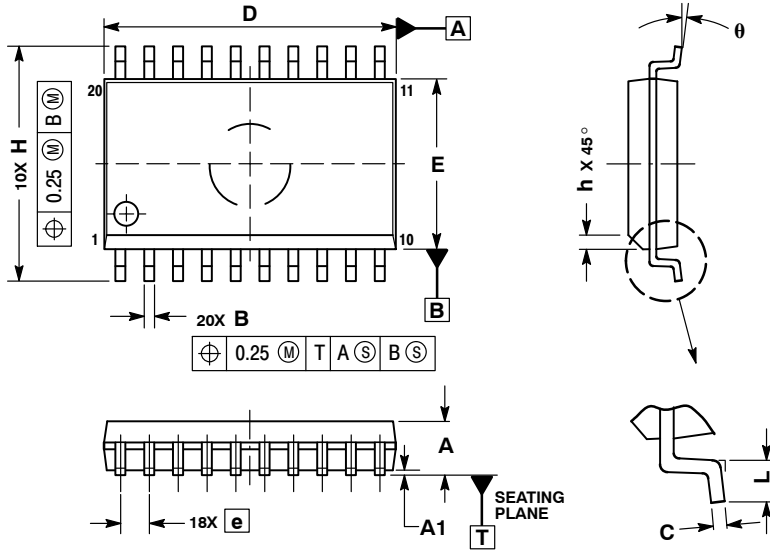


Figure 9. INPUT EQUIVALENT CIRCUIT

# MC74VHC374

## PACKAGE DIMENSIONS

SOIC-20  
DW SUFFIX  
CASE 751D-05  
ISSUE G



NOTES:

1. DIMENSIONS ARE IN MILLIMETERS.
2. INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 1994.
3. DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.
5. DIMENSION B DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF B DIMENSION AT MAXIMUM MATERIAL CONDITION.

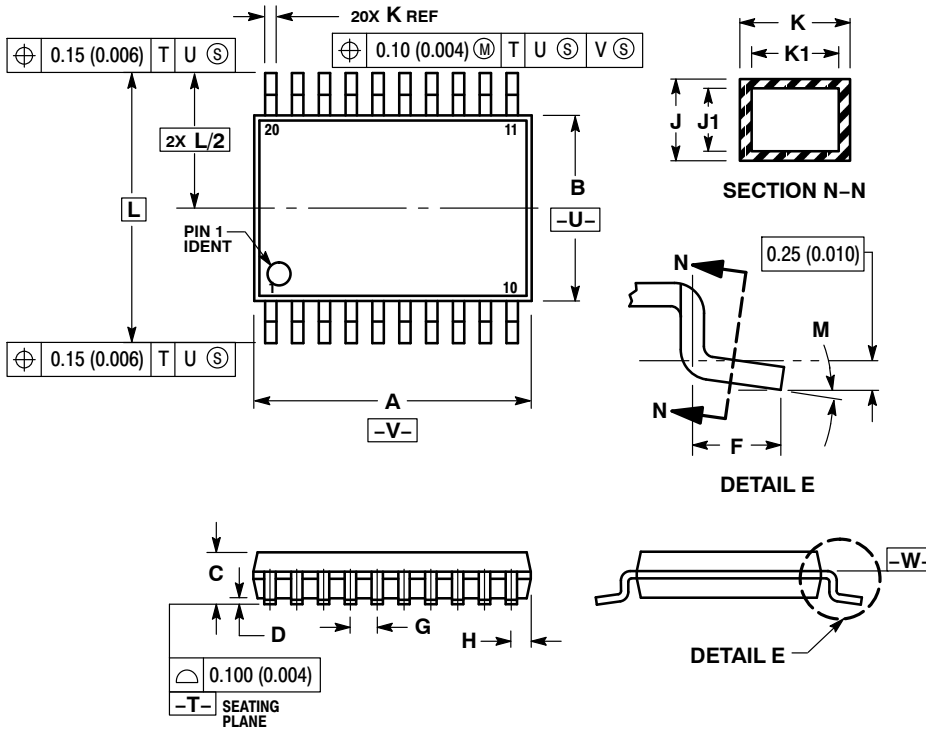
DIM	MILLIMETERS	
	MIN	MAX
A	2.35	2.65
A1	0.10	0.25
B	0.35	0.49
C	0.23	0.32
D	12.65	12.95
E	7.40	7.60
e	1.27 BSC	
H	10.05	10.55
h	0.25	0.75
L	0.50	0.90
θ	0°	7°



# MC74VHC374

## PACKAGE DIMENSIONS

TSSOP-20  
CASE 948E-02  
ISSUE C



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	6.40	6.60	0.252	0.260
B	4.30	4.50	0.169	0.177
C	---	1.20	---	0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
H	0.27	0.37	0.011	0.015
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
M	0°	8°	0°	8°

### SOLDERING FOOTPRINT

